

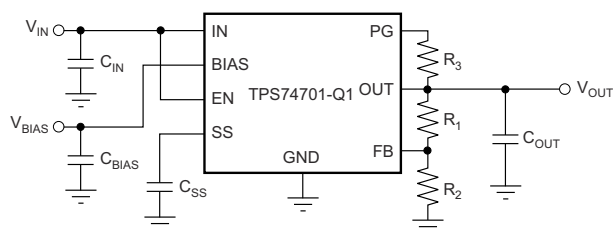
TPS74701-Q1 車載対応、プログラマブル・ソフトスタート機能搭載 500mA 低ドロップアウト・リニア・レギュレータ

1 特長

- 車載アプリケーション用に AEC-Q100 認定済み:
 - 温度グレード 1: $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$, T_A
- V_{OUT} 範囲: $0.8\text{V} \sim 3.6\text{V}$
- V_{IN} 範囲: $0.8\text{V} \sim 5.5\text{V}$
- V_{BIAS} 範囲: $2.7\text{V} \sim 5.5\text{V}$
- 低いドロップアウト: 20mV (500mA 時標準値), $V_{\text{BIAS}} = 5\text{V}$
- パワー・グッド (PG) 出力により、電源電圧を監視し、他の電源のシーケンシング信号を供給
- ライン、負荷、温度の全範囲にわたって 0.95% の精度
- プログラム可能なソフト・スタートにより、直線的に電圧が立ち上がるようにスタートアップさせることが可能
- V_{BIAS} により、過渡応答性に優れた低 V_{IN} 動作を実現
- 任意の出力コンデンサ ($\geq 2.2\mu\text{F}$) で安定的に動作
- $3\text{mm} \times 3\text{mm}$ の小型 10 ピン VSON パッケージで供給

2 アプリケーション

- 車載ヘッド・ユニット
- インフォテインメントおよびクラスタ
- テレマティクス制御ユニット
- 前方および後方カメラ



代表的なアプリケーション回路 (可変)

3 概要

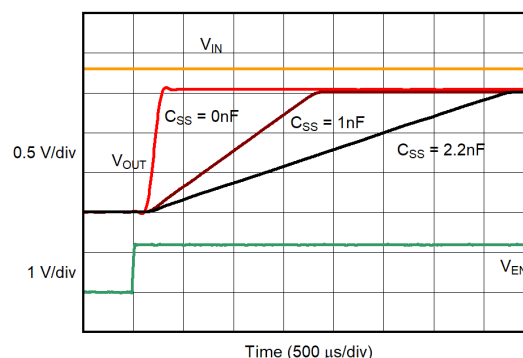
TPS74701-Q1 低ドロップアウト (LDO) リニア・レギュレータは、広範なアプリケーション向けの使いやすく堅牢な電力管理ソリューションを実現します。ソフトスタートをユーザーがプログラム可能なため、容量性突入電流を低減して入力電源のストレスを最小限に抑えることができ、単調なスタートアップ機能は多くの種類のプロセッサおよび ASIC に電力を供給するように設計されています。イネーブル入力とパワー・グッド出力により、外部レギュレータとのシーケンシングが簡単になり、特殊なスタートアップ要件を持つ広範なアプリケーションのシーケンシング要件を満たすソリューションを構成できます。

高精度の基準電圧およびエラー・アンプは、負荷、ライン、温度、プロセスの全体にわたって 0.95% の精度を維持します。このデバイスは $2.2\mu\text{F}$ 以上のあらゆる種類のコンデンサで安定動作し、AEC-Q100 に従って完全に規定されています。

パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイズ (2)
TPS74701-Q1	DRC (VSON, 10)	$3\text{mm} \times 3\text{mm}$

- 詳細については、「[メカニカル、パッケージ、および注文情報](#)」を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。



ターンオン応答



Table of Contents

1 特長	1	6.4 Device Functional Modes.....	18
2 アプリケーション	1	7 Application and Implementation	19
3 概要	1	7.1 Application Information.....	19
4 Pin Configuration and Functions	3	7.2 Typical Application.....	19
5 Specifications	4	7.3 Power Supply Recommendations.....	22
5.1 Absolute Maximum Ratings.....	4	7.4 Layout.....	22
5.2 ESD Ratings.....	4	8 Device and Documentation Support	26
5.3 Recommended Operating Conditions.....	4	8.1 Device Support.....	26
5.4 Thermal Information.....	5	8.2 ドキュメントの更新通知を受け取る方法.....	26
5.5 Electrical Characteristics.....	6	8.3 サポート・リソース.....	26
5.6 Typical Characteristics: $I_{OUT} = 50\text{ mA}$	8	8.4 Trademarks.....	26
5.7 Typical Characteristics: $V_{EN} = V_{IN} = 1.8\text{ V}$, V_{OUT} = 1.5 V.....	13	8.5 静電気放電に関する注意事項.....	26
6 Detailed Description	15	8.6 用語集.....	26
6.1 Overview.....	15	9 Revision History	27
6.2 Functional Block Diagram.....	15	10 Mechanical, Packaging, and Orderable Information	27
6.3 Feature Description.....	15		

4 Pin Configuration and Functions

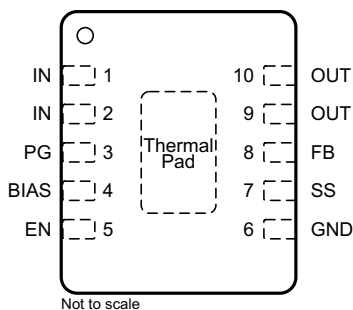


図 4-1. DRC Package, 10-Pin VSON (Top View)

表 4-1. Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
BIAS	4	I	Bias pin. Input voltage for error amplifier, reference, and internal control circuits.
EN	5	I	Enable pin. Driving this pin high enables the regulator. Driving this pin low puts the regulator into shutdown mode. This pin must not be left unconnected.
FB	8	I	Feedback pin. The feedback connection to the center tap of an external resistor divider network that sets the output voltage. This pin must not be left floating.
GND	6	—	Ground pin.
IN	1, 2	I	Input pin. This pin supplies the input voltage to the device. For best transient response and to minimize input impedance, use the recommended value or larger capacitor from IN to GND, as listed in the Recommended Operating Conditions table. Place the input capacitors as close as possible to the IN and GND pins of the device.
OUT	9, 10	O	Output pin. Regulated output voltage, a small capacitor (total typical capacitance $\geq 2.2 \mu\text{F}$, ceramic) is needed from this pin to ground to assure stability. Place the output capacitors as close as possible to the OUT and GND pins of the device.
PG	3	O	Power-good pin. This pin is an open-drain, active-high output that indicates the status of V_{OUT} ; see the Power Good section for additional information.
SS	7	—	Soft-start pin. A capacitor connected on this pin to ground sets the start-up time. If this pin is left unconnected, the regulator output soft-start ramp time is typically 200 μs ; see the Programmable Soft-Start section for further information.
Thermal Pad	—	—	Connect the pad to GND for the best possible thermal performance.

5 Specifications

5.1 Absolute Maximum Ratings

over operating temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{IN} , V_{BIAS}	Input voltage	-0.3	6	V
V_{EN}	Enable voltage	-0.3	6	V
V_{PG}	Power good voltage	-0.3	6	V
I_{PG}	PG sink current	0	1.5	mA
V_{SS}	Soft-start voltage	-0.3	6	V
V_{FB}	Feedback voltage	-0.3	6	V
V_{OUT}	Output voltage	-0.3	$V_{IN} + 0.3$ ⁽²⁾	V
I_{OUT}	Output current	Internally limited		
I_{CL}	Output short-circuit duration	Indefinite		
P_{DISS}	Continuous total power dissipation	See Thermal Information		
T_J , T_{stg}	Junction temperature	-40	150	°C
	Storage temperature	-55	150	

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The absolute maximum rating is $V_{IN} + 0.3$ V or 6.0 V, whichever is smaller.

5.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000
		Charged device model (CDM), per AEC specification Q100-011	±500

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IN}	Input supply voltage	$V_{OUT} + V_{DO}$ (V_{IN})	$V_{OUT} + 0.3$	5.5	V
V_{EN}	Enable supply voltage		V_{IN}	5.5	V
V_{BIAS} ⁽¹⁾	Bias supply voltage	$V_{OUT} + V_{DO}$ (V_{BIAS}) ⁽²⁾	$V_{OUT} + 1.6$ ⁽²⁾	5.5	V
V_{OUT}	Output voltage	0.8		3.3	V
I_{OUT}	Output current	0		500	mA
C_{OUT}	Output capacitor	2.2			μF
C_{IN} ⁽³⁾	Input capacitor	1			μF
C_{BIAS}	Bias capacitor	0.1	1		μF
T_J	Operating junction temperature	-40		150	°C

- (1) BIAS supply is required when V_{IN} is below $V_{OUT} + 1.62$ V.
- (2) V_{BIAS} has a minimum voltage of 2.7 V or $V_{OUT} + V_{DO}$ (V_{BIAS}), whichever is higher.
- (3) If V_{IN} and V_{BIAS} are connected to the same supply, the recommended minimum capacitor for the supply is 4.7 μF.

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS74701-Q1		UNIT
		DRC (VSON)	DRC (VSON) ⁽²⁾	
		10 PINS	10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	41.5	47.2	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	78	63.7	°C/W
R _{θJB}	Junction-to-board thermal resistance	N/A	19.5	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.7	4.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	11.3	19.4	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	6.6	3.3	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application note](#).
 (2) New chip.

5.5 Electrical Characteristics

at $V_{EN} = 1.1\text{ V}$, $V_{IN} = V_{OUT} + 0.3\text{ V}$, $C_{BIAS} = 0.1\text{ }\mu\text{F}$, $C_{IN} = C_{OUT} = 10\text{ }\mu\text{F}$, $C_{NR} = 1\text{ nF}$, $I_{OUT} = 50\text{ mA}$, $V_{BIAS} = 5.0\text{ V}$, and $T_J = -40^\circ\text{C}$ to 125°C (Legacy Chip) and $T_J = -40^\circ\text{C}$ to 150°C (New Chip), (unless otherwise noted); typical values are at $T_J = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{REF}	Internal reference (Adj.)	$T_A = +25^\circ\text{C}$	0.796	0.8	0.804	V
V_{OUT}	Output voltage range	$V_{IN} = 5\text{ V}$, $I_{OUT} = 0.5\text{ A}$	V_{REF}		3.6	V
	Accuracy ⁽¹⁾	$2.97\text{ V} \leq V_{BIAS} \leq 5.5\text{ V}$, $50\text{ mA} \leq I_{OUT} \leq 0.5\text{ A}$ (Legacy Chip)	-2	± 0.5	2	%
		$2.97\text{ V} \leq V_{BIAS} \leq 5.5\text{ V}$, $50\text{ mA} \leq I_{OUT} \leq 0.5\text{ A}$ (New Chip)	-1.25	± 0.3	1.25	
$\Delta V_{OUT} (\Delta V_{IN})$	Line regulation	$V_{OUT(nom)} + 0.3 \leq V_{IN} \leq 5.5\text{ V}$ (Legacy Chip)		0.03		% / V
		$V_{OUT(nom)} + 0.3 \leq V_{IN} \leq 5.5\text{ V}$ (New Chip)		0.001		
$\Delta V_{OUT} (\Delta I_{OUT})$	Load regulation	$50\text{ mA} \leq I_{OUT} \leq 0.5\text{ A}$ (Legacy Chip)		0.09		% / A
		$50\text{ mA} \leq I_{OUT} \leq 0.5\text{ A}$ (New Chip)		0.11		
V_{DO}	V_{IN} dropout voltage ⁽²⁾	$I_{OUT} = 0.5\text{ A}$, $V_{BIAS} - V_{OUT(nom)} \geq 1.62\text{ V}$ (Legacy Chip) ⁽³⁾		50	120	mV
		$I_{OUT} = 0.5\text{ A}$, $V_{BIAS} - V_{OUT(nom)} \geq 1.62\text{ V}$ (New Chip) ⁽³⁾		20	40	
	V_{BIAS} dropout voltage ⁽²⁾	$I_{OUT} = 0.5\text{ A}$, $V_{IN} = V_{BIAS}$ (Legacy Chip)		1.31	1.39	V
		$I_{OUT} = 0.5\text{ A}$, $V_{IN} = V_{BIAS}$ (New Chip)		1.1	1.3	
I_{CL}	Output current limit	$V_{OUT} = 80\% \times V_{OUT(nom)}$ (Legacy Chip)	800		1350	mA
		$V_{OUT} = 80\% \times V_{OUT(nom)}$ (New Chip)	800		1350	
I_{BIAS}	BIAS pin current	(Legacy Chip)		1	2	mA
		(New Chip)		1	1.2	
I_{SHDN}	Shutdown supply current (I_{GND})	$V_{EN} \leq 0.4\text{ V}$ (Legacy Chip)		1	50	μA
		$V_{EN} \leq 0.4\text{ V}$ (New Chip)		1	10	
I_{FB}	Feedback pin current	(Legacy Chip)	-1	0.15	1	μA
		(New Chip)	-30	0.15	30	nA
PSRR	Power-supply rejection (V_{IN} to V_{OUT})	1 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (Legacy Chip)		60		dB
		1 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (New Chip)		76		
		300 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (Legacy Chip)		30		
		300 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (New Chip)		50		
	Power-supply rejection (V_{BIAS} to V_{OUT})	1 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (Legacy Chip)		50		
		1 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (New Chip)		59		
		300 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (Legacy Chip)		30		
		300 kHz, $I_{OUT} = 0.5\text{ A}$, $V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (New Chip)		49		
V_n	Output noise voltage	BW = 100 Hz to 100 kHz, $I_{OUT} = 0.5\text{ A}$, $C_{SS} = 1\text{ nF}$ (Legacy Device)		$25 \times V_{OUT}$		μV_{rms}
		BW = 100 Hz to 100 kHz, $I_{OUT} = 0.5\text{ A}$, $C_{SS} = 1\text{ nF}$ (New Chip)		$20 \times V_{OUT}$		
t_{STR}	Minimum startup time	R_{LOAD} for $I_{OUT} = 0.5\text{ A}$, $C_{SS} = \text{open}$ (Legacy Device)		200		μs
		R_{LOAD} for $I_{OUT} = 0.5\text{ A}$, $C_{SS} = \text{open}$ (New Chip)		250		

5.5 Electrical Characteristics (続き)

at $V_{EN} = 1.1\text{ V}$, $V_{IN} = V_{OUT} + 0.3\text{ V}$, $C_{BIAS} = 0.1\text{ }\mu\text{F}$, $C_{IN} = C_{OUT} = 10\text{ }\mu\text{F}$, $C_{NR} = 1\text{ nF}$, $I_{OUT} = 50\text{ mA}$, $V_{BIAS} = 5.0\text{ V}$, and $T_J = -40^\circ\text{C}$ to 125°C (Legacy Chip) and $T_J = -40^\circ\text{C}$ to 150°C (New Chip), (unless otherwise noted); typical values are at $T_J = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{SS}	Soft-start charging current	$V_{SS} = 0.4\text{ V}$ (Legacy Chip)		440		nA
		$V_{SS} = 0.4\text{ V}$ (New Chip)		530		
$V_{EN(hi)}$	Enable input high level		1.1		5.5	V
$V_{EN(lo)}$	Enable input low level		0		0.4	V
$V_{EN(hys)}$	Enable pin hysteresis	(Legacy Chip)		50		mV
		(New Chip)		55		
$V_{EN(dg)}$	Enable pin deglitch time			20		μs
I_{EN}	Enable pin current	$V_{EN} = 5\text{ V}$ (Legacy Chip)		0.1	1	μA
		$V_{EN} = 5\text{ V}$ (New Chip)		0.1	0.3	
V_{IT}	PG trip threshold	V_{OUT} decreasing	85	90	94	$\%V_{OUT}$
V_{HYS}	PG trip hysteresis			3		$\%V_{OUT}$
$V_{PG(lo)}$	PG output low voltage	$I_{PG} = 1\text{ mA}$ (sinking), $V_{OUT} < V_{IT}$ (Legacy Chip)			0.3	V
		$I_{PG} = 1\text{ mA}$ (sinking), $V_{OUT} < V_{IT}$ (New Chip)			0.125	
$I_{PG(Ik)}$	PG leakage current	$V_{PG} = 5.25\text{ V}$, $V_{OUT} > V_{IT}$ (Legacy Chip)		0.1	1	μA
		$V_{PG} = 5.25\text{ V}$, $V_{OUT} > V_{IT}$ (New Chip)		0.1	0.05	
T_{SD}	Thermal shutdown temperature	Shutdown, temperature increasing		165		$^\circ\text{C}$
		Reset, temperature decreasing		140		

- (1) Adjustable devices tested at 0.8 V; resistor tolerance is not taken into account.
- (2) Dropout is defined as the voltage from V_{IN} to V_{OUT} when V_{OUT} is 3% below nominal.
- (3) 1.62 V is a test condition of this device and can be adjusted by referring to Figure 5-29.

5.6 Typical Characteristics: $I_{OUT} = 50\text{ mA}$

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3\text{ V}$, $V_{BIAS} = 5\text{ V}$, $I_{OUT} = 50\text{ mA}$, $V_{EN} = V_{IN}$, $C_{IN} = 1\text{ }\mu\text{F}$, $C_{BIAS} = 4.7\text{ }\mu\text{F}$, and $C_{OUT} = 10\text{ }\mu\text{F}$ (unless otherwise noted)

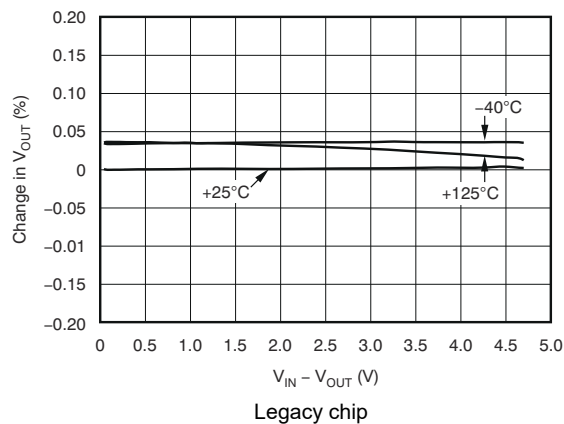


图 5-1. V_{IN} Line Regulation

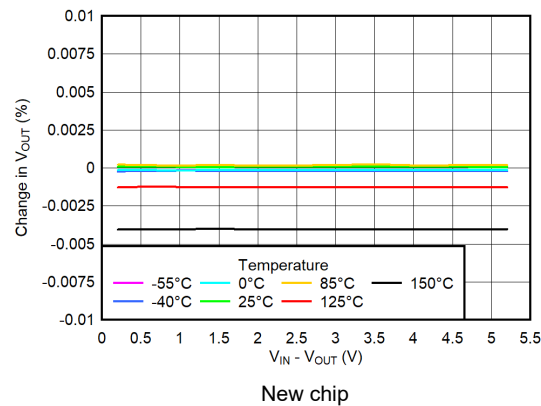


图 5-2. V_{IN} Line Regulation

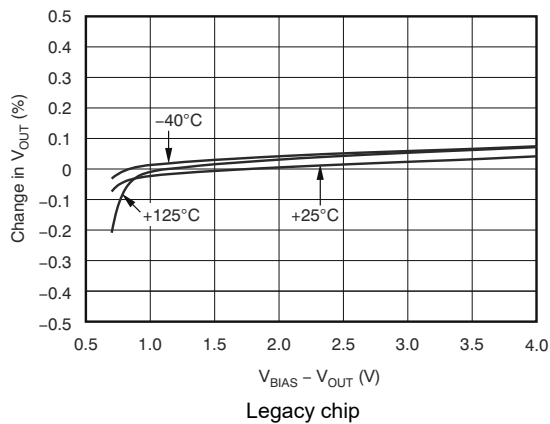


图 5-3. V_{BIAS} Line Regulation

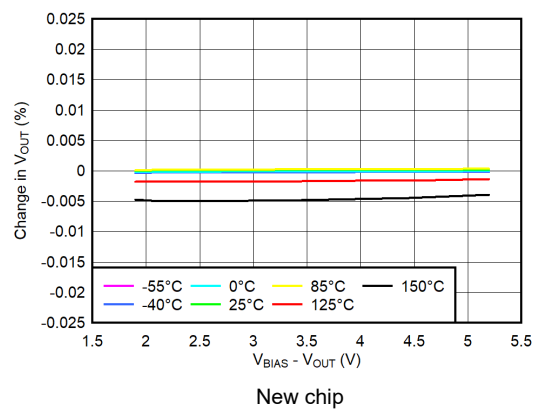


图 5-4. V_{BIAS} Line Regulation

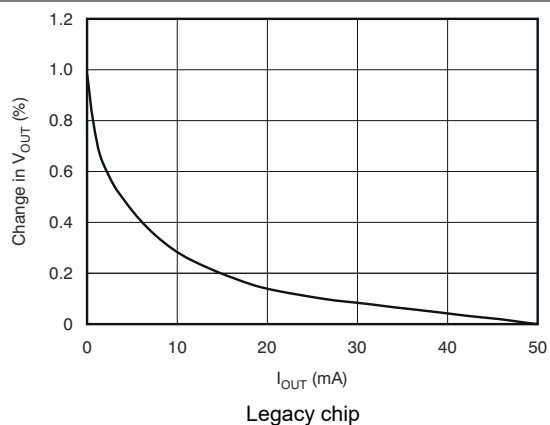


图 5-5. Load Regulation at Light Load

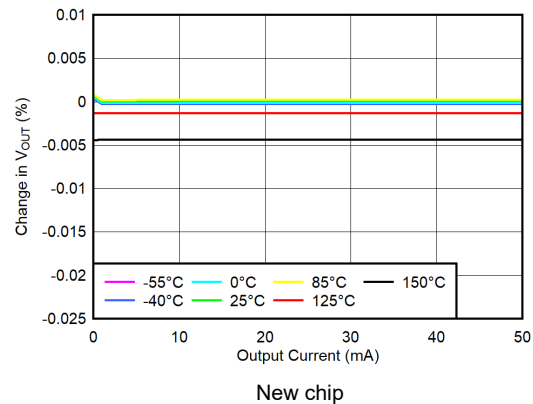


图 5-6. Load Regulation at Light Load

5.6 Typical Characteristics: $I_{OUT} = 50 \text{ mA}$ (continued)

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3 \text{ V}$, $V_{BIAS} = 5 \text{ V}$, $I_{OUT} = 50 \text{ mA}$, $V_{EN} = V_{IN}$, $C_{IN} = 1 \mu\text{F}$, $C_{BIAS} = 4.7 \mu\text{F}$, and $C_{OUT} = 10 \mu\text{F}$ (unless otherwise noted)

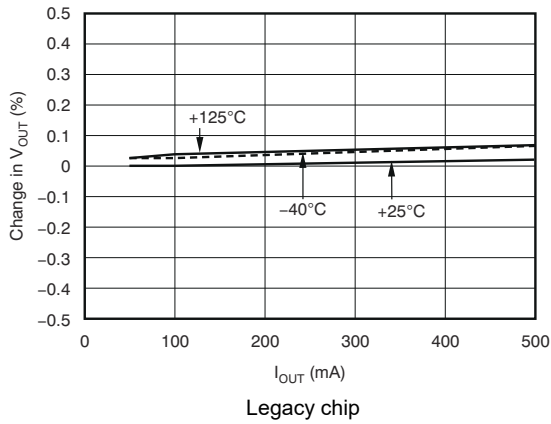


Figure 5-7. Load Regulation

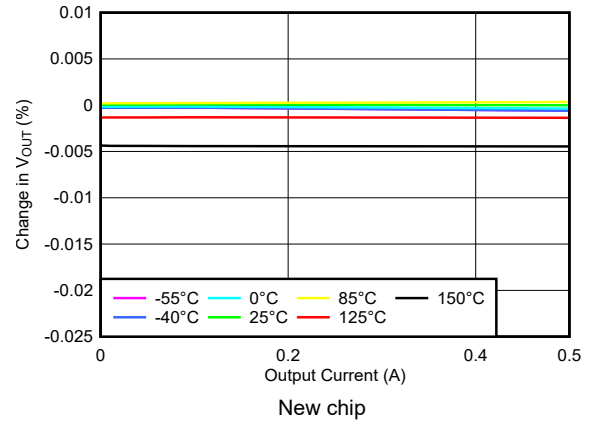


Figure 5-8. Load Regulation

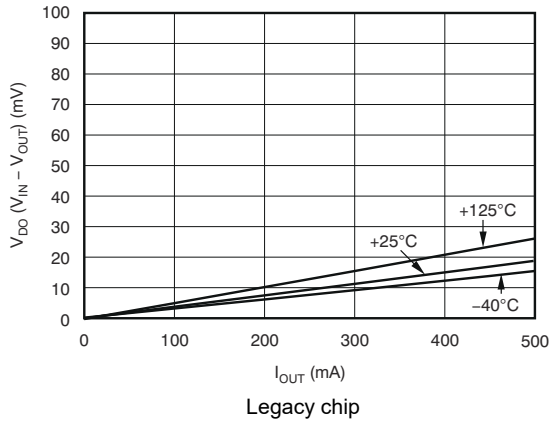


Figure 5-9. Dropout Voltage vs I_{OUT} and Temperature (T_J)

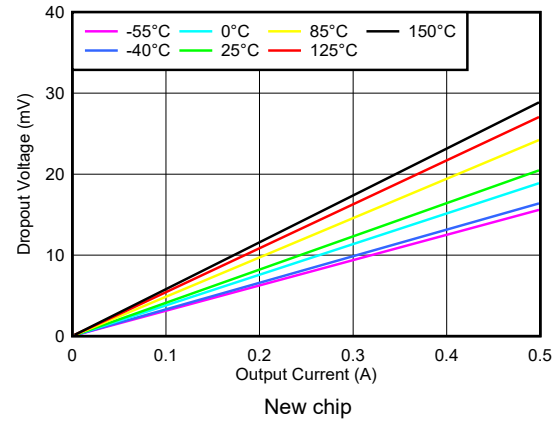


Figure 5-10. V_{IN} Dropout Voltage vs I_{OUT} and Temperature (T_J)

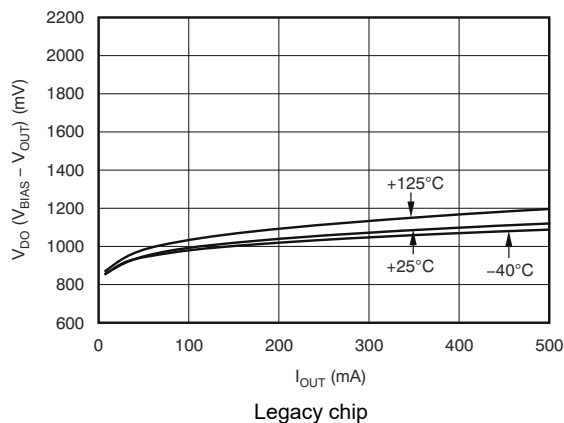


Figure 5-11. V_{BIAS} Dropout Voltage vs I_{OUT} and Temperature (T_J)

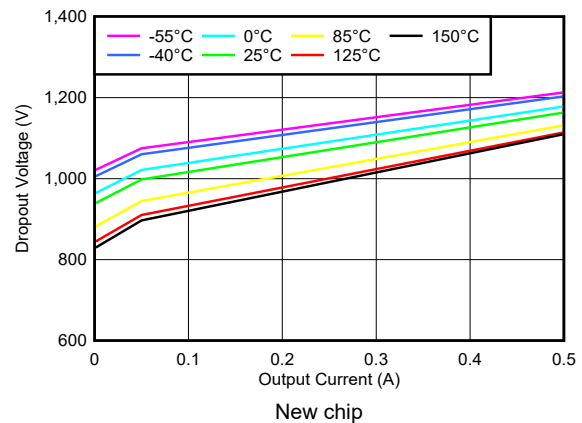


Figure 5-12. V_{BIAS} Dropout Voltage vs I_{OUT} and Temperature (T_J)

5.6 Typical Characteristics: $I_{OUT} = 50\text{ mA}$ (continued)

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3\text{ V}$, $V_{BIAS} = 5\text{ V}$, $I_{OUT} = 50\text{ mA}$, $V_{EN} = V_{IN}$, $C_{IN} = 1\text{ }\mu\text{F}$, $C_{BIAS} = 4.7\text{ }\mu\text{F}$, and $C_{OUT} = 10\text{ }\mu\text{F}$ (unless otherwise noted)

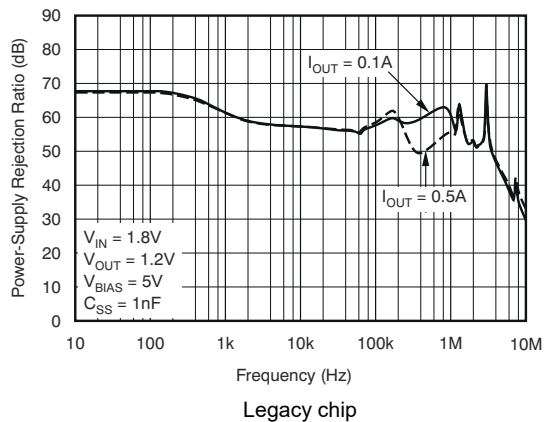


Figure 5-13. V_{BIAS} PSRR vs Frequency

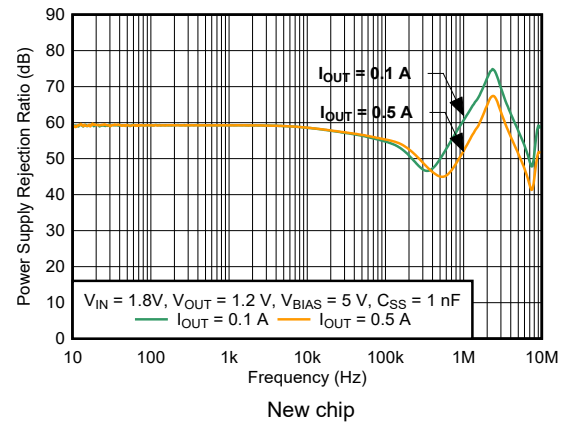


Figure 5-14. V_{BIAS} PSRR vs Frequency

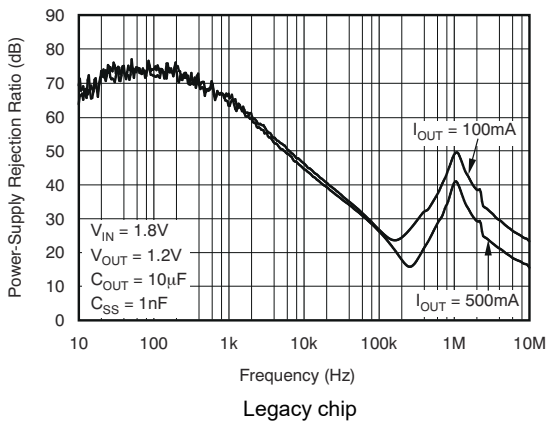


Figure 5-15. V_{IN} PSRR vs Frequency

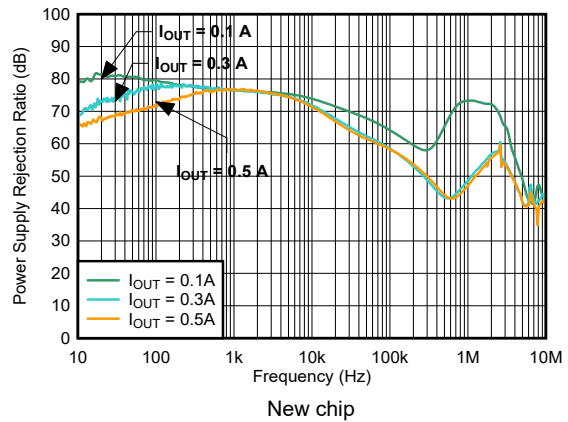


Figure 5-16. V_{IN} PSRR vs Frequency

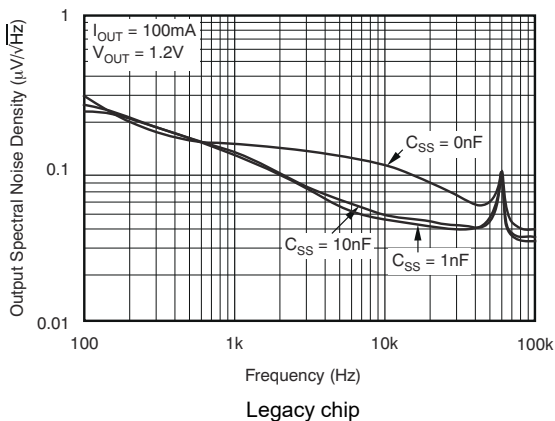


Figure 5-17. Noise Spectral Density

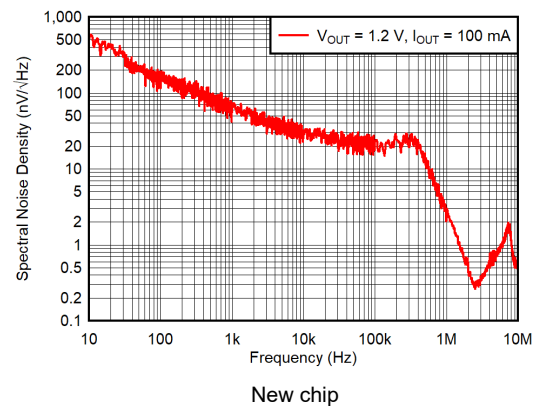


Figure 5-18. Noise Spectral Density

5.6 Typical Characteristics: $I_{OUT} = 50 \text{ mA}$ (continued)

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3 \text{ V}$, $V_{BIAS} = 5 \text{ V}$, $I_{OUT} = 50 \text{ mA}$, $V_{EN} = V_{IN}$, $C_{IN} = 1 \mu\text{F}$, $C_{BIAS} = 4.7 \mu\text{F}$, and $C_{OUT} = 10 \mu\text{F}$ (unless otherwise noted)

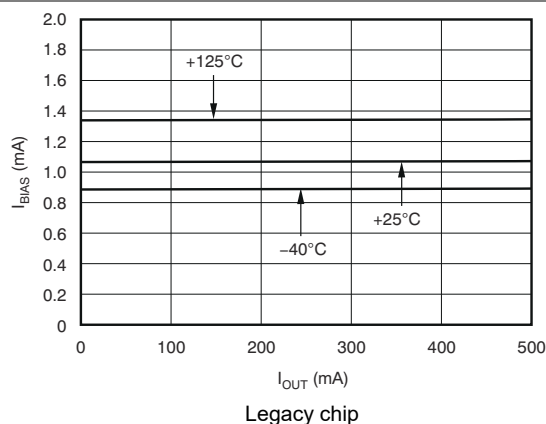


Figure 5-19. BIAS Pin Current vs I_{OUT} and Temperature (T_J)

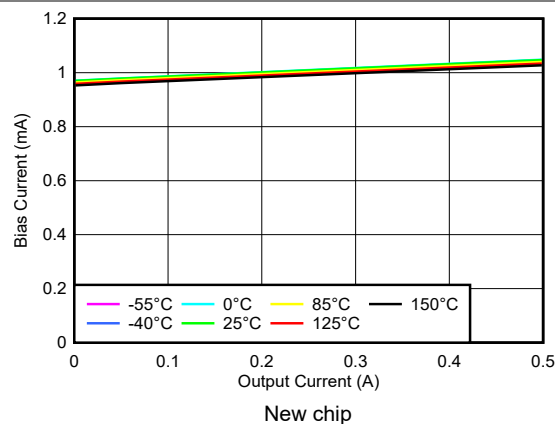


Figure 5-20. BIAS Pin Current vs Output Current and Temperature (T_J)

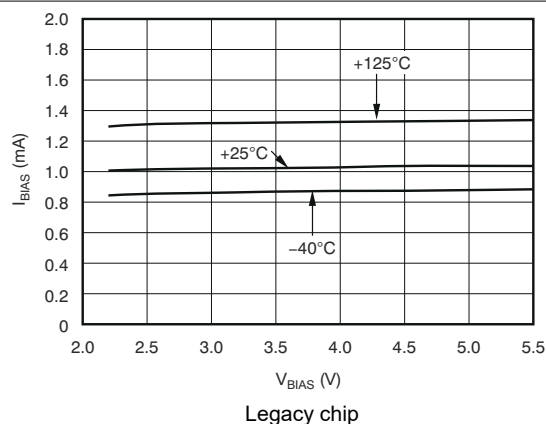


Figure 5-21. BIAS Pin Current vs V_{BIAS} and Temperature (T_J)

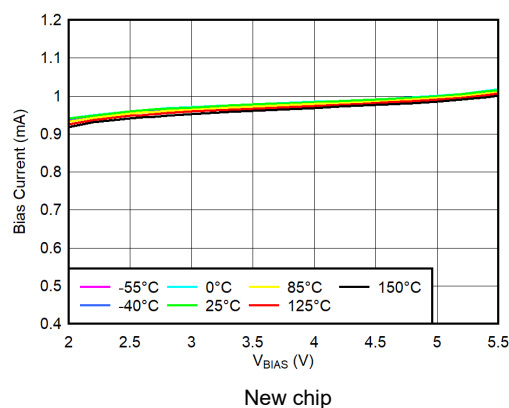


Figure 5-22. BIAS Pin Current vs V_{BIAS} and Temperature (T_J)

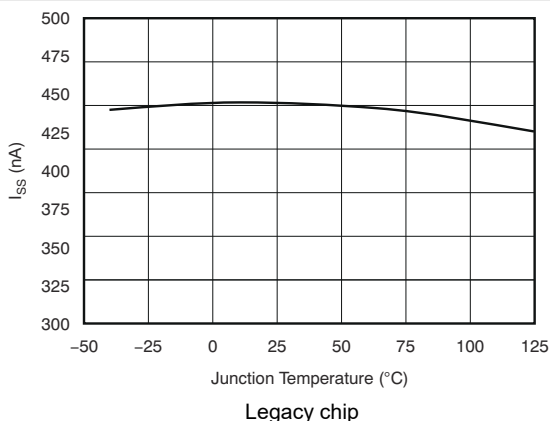


Figure 5-23. Soft-Start Charging Current (I_{SS}) vs Temperature (T_J)

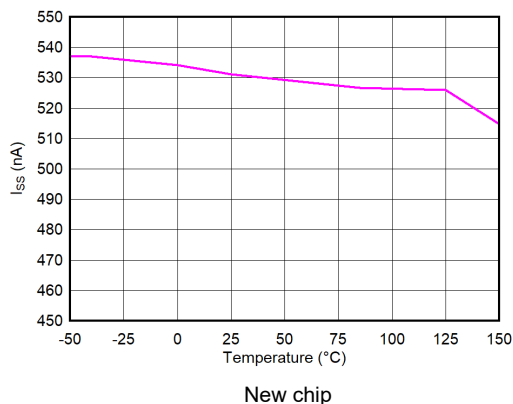


Figure 5-24. Soft-Start Charging Current (I_{SS}) vs Temperature (T_J)

5.6 Typical Characteristics: $I_{OUT} = 50\text{ mA}$ (continued)

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3\text{ V}$, $V_{BIAS} = 5\text{ V}$, $I_{OUT} = 50\text{ mA}$, $V_{EN} = V_{IN}$, $C_{IN} = 1\text{ }\mu\text{F}$, $C_{BIAS} = 4.7\text{ }\mu\text{F}$, and $C_{OUT} = 10\text{ }\mu\text{F}$ (unless otherwise noted)

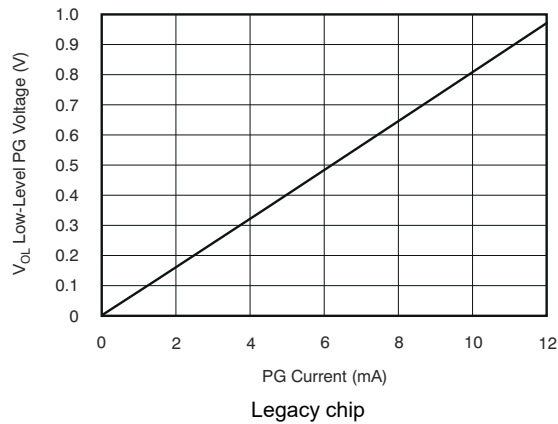


Figure 5-25. Low-Level PG Voltage vs Current

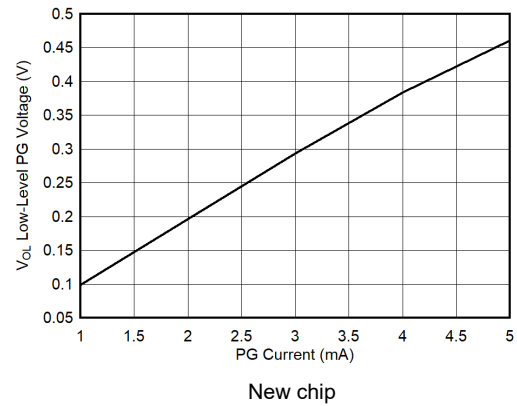


Figure 5-26. Low-Level PG Voltage vs Current

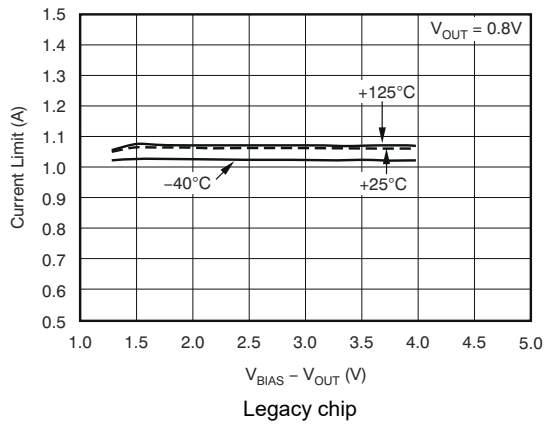


Figure 5-27. Current Limit vs ($V_{BIAS} - V_{OUT}$)

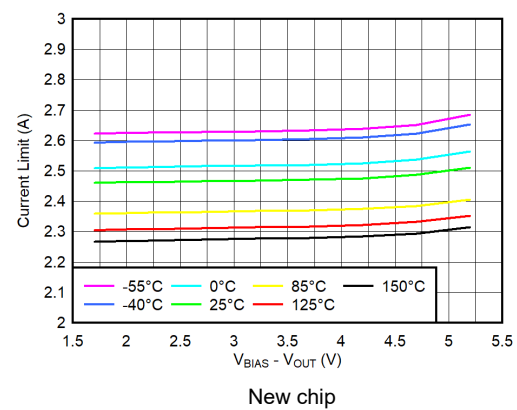


Figure 5-28. Current Limit vs ($V_{BIAS} - V_{OUT}$)

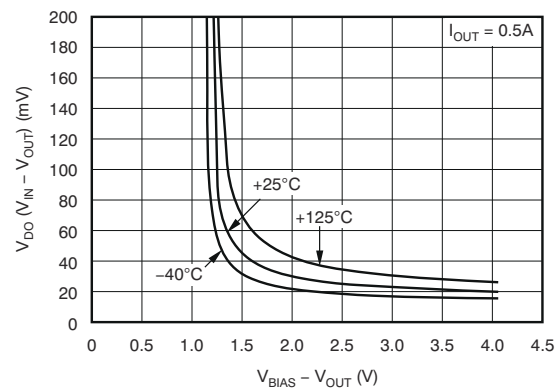


Figure 5-29. Dropout Voltage vs ($V_{BIAS} - V_{OUT}$) and Temperature (T_J)

5.7 Typical Characteristics: $V_{EN} = V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3\text{ V}$, $V_{BIAS} = 5\text{ V}$, $I_{OUT} = 50\text{ mA}$, $V_{EN} = V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$, $C_{IN} = 1\text{ }\mu\text{F}$, $C_{BIAS} = 4.7\text{ }\mu\text{F}$, and $C_{OUT} = 10\text{ }\mu\text{F}$ (unless otherwise noted)

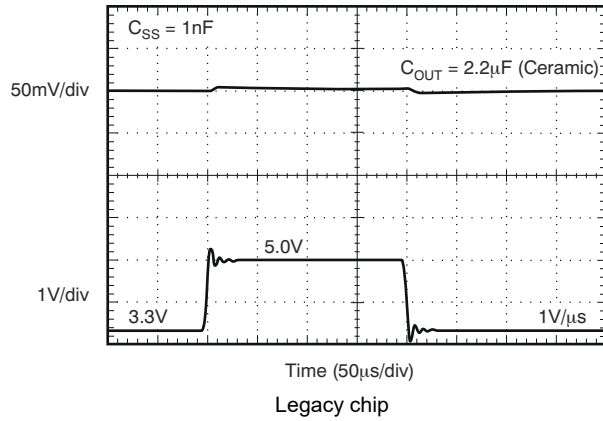


Figure 5-30. V_{BIAS} Line Transient

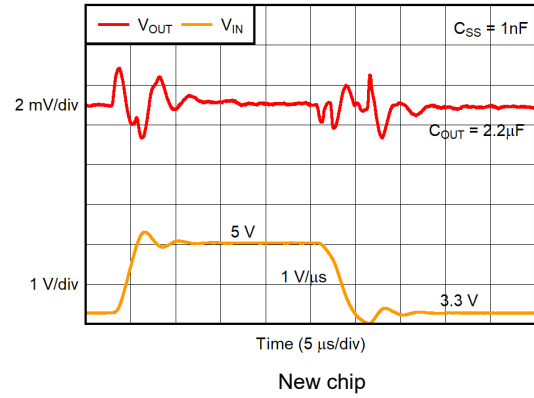


Figure 5-31. V_{BIAS} Line Transient

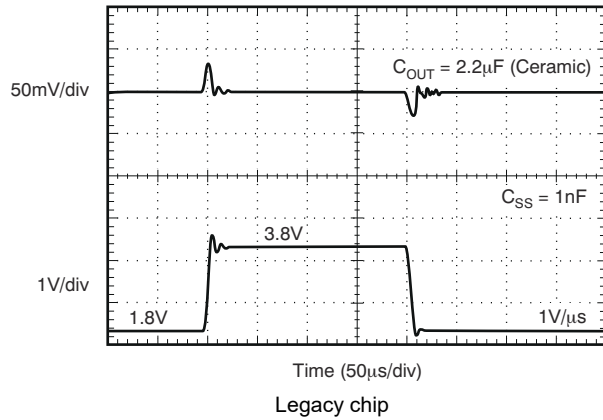


Figure 5-32. V_{IN} Line Transient

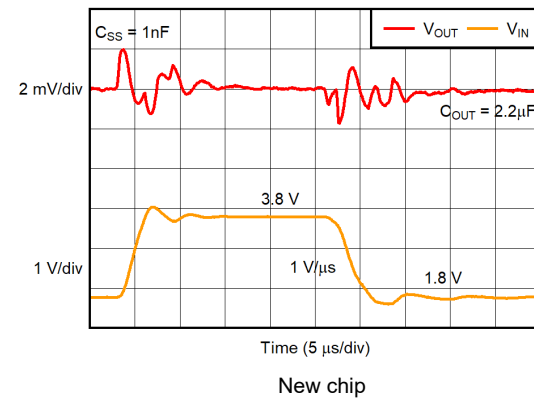


Figure 5-33. V_{IN} Line Transient

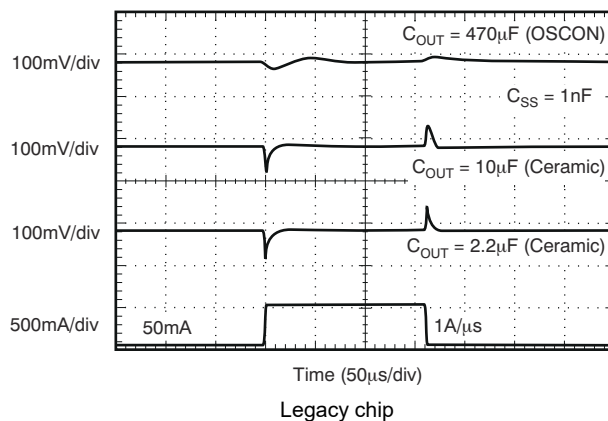


Figure 5-34. Output Load Transient Response

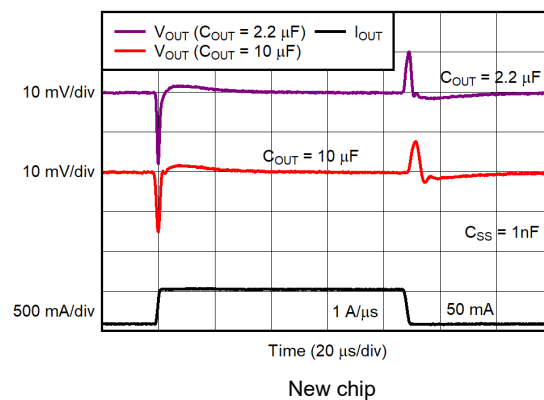


Figure 5-35. Output Load Transient Response

5.7 Typical Characteristics: $V_{EN} = V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$ (continued)

at $T_J = 25^\circ\text{C}$, $V_{IN} = V_{OUT(TYP)} + 0.3\text{ V}$, $V_{BIAS} = 5\text{ V}$, $I_{OUT} = 50\text{ mA}$, $V_{EN} = V_{IN} = 1.8\text{ V}$, $V_{OUT} = 1.5\text{ V}$, $C_{IN} = 1\text{ }\mu\text{F}$, $C_{BIAS} = 4.7\text{ }\mu\text{F}$, and $C_{OUT} = 10\text{ }\mu\text{F}$ (unless otherwise noted)

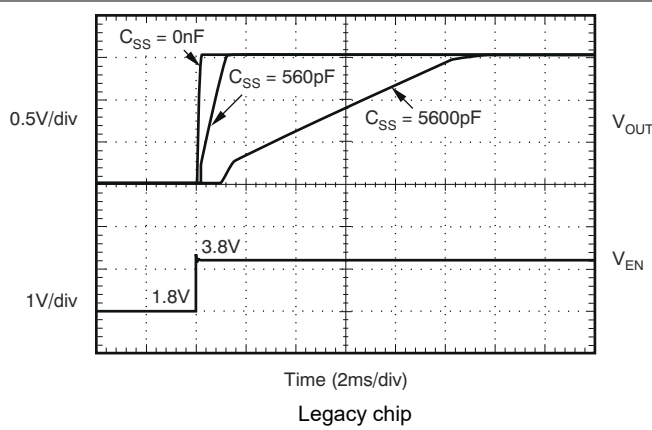


Figure 5-36. Turn-On Response

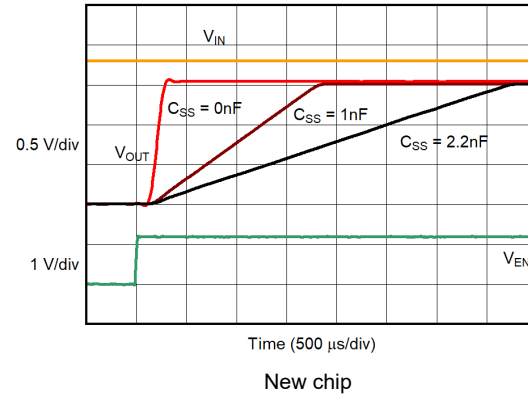


Figure 5-37. Turn-On Response

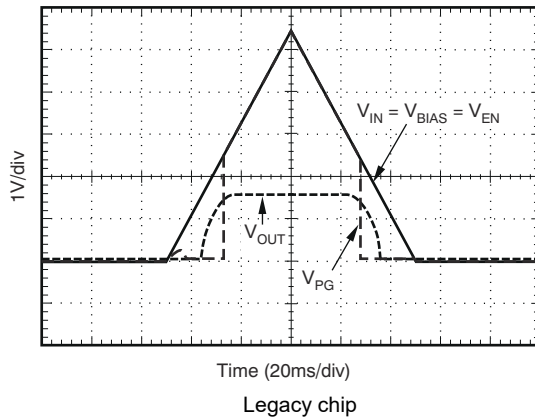


Figure 5-38. Power-Up and Power-Down

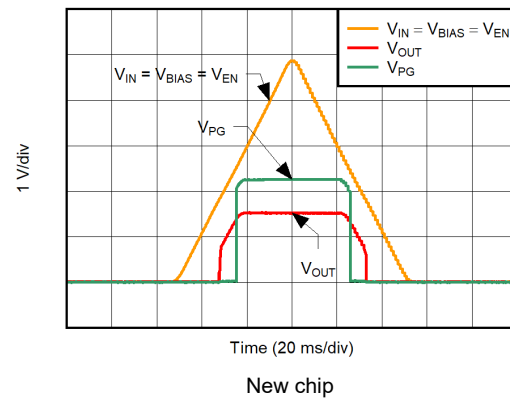


Figure 5-39. Power-Up and Power-Down

6 Detailed Description

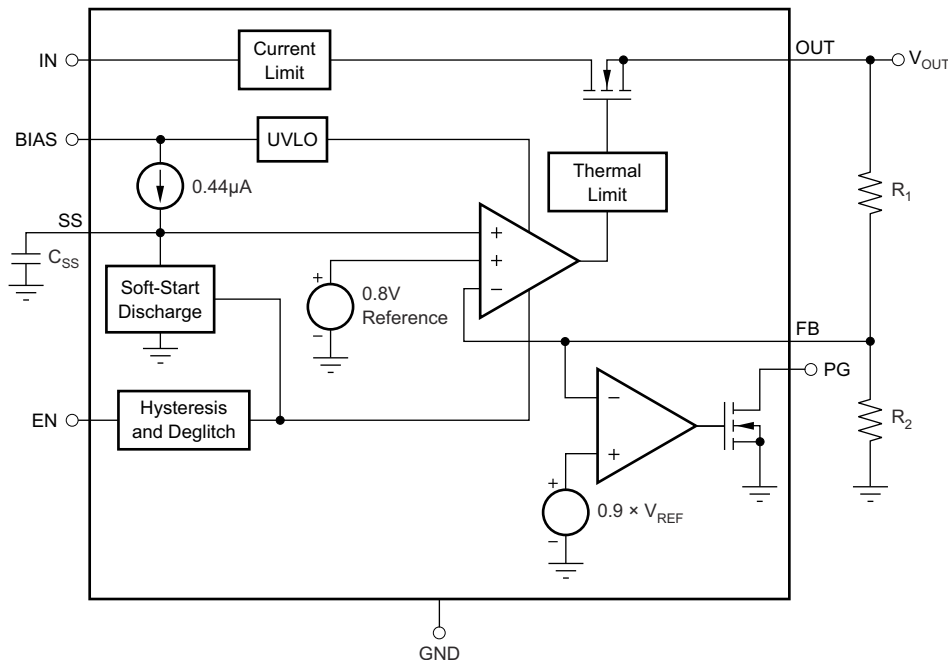
6.1 Overview

The TPS74701-Q1 is a low-dropout regulator that features soft-start capability. This regulator uses a low current bias input to power all internal control circuitry, allowing the NMOS pass transistor to regulate very low input and output voltages.

The use of an NMOS-pass transistor offers several critical advantages for many applications. Unlike a PMOS topology device, the output capacitor has little effect on loop stability. This architecture allows the TPS74701 to be stable with any capacitor type of value 2.2 μF or greater. Transient response is also superior to PMOS topologies, particularly for low VIN applications.

The TPS74701-Q1 features a programmable voltage-controlled soft-start circuit that provides a smooth, monotonic start-up and limits start-up inrush currents that may be caused by large capacitive loads. A power-good (PG) output is available to allow supply monitoring and sequencing of other supplies. An enable (EN) pin with hysteresis and deglitch allows slow-ramping signals to be used for sequencing the device. The low VIN and VOUT capability allows for inexpensive, easy-to-design, and efficient linear regulation between the multiple supply voltages often present in processor-intensive systems.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Transient Response

The TPS74701-Q1 is designed to have excellent transient response for most applications with a small amount of output capacitance. In some cases, the transient response can be limited by the transient response of the input supply. This limitation is especially true in applications where the difference between the input and output is less than 300 mV. In this case, adding additional input capacitance improves the transient response much more than just adding additional output capacitance does. With a solid input supply, adding additional output capacitance reduces undershoot and overshoot during a transient event; see [Figure 5-34](#) and [Figure 5-34](#). Because the TPS74701-Q1 is stable with output capacitors as low as 2.2 μF , many applications can then need very little capacitance at the LDO output. For these applications, local bypass capacitance for the powered device can be sufficient to meet the transient requirements of the application. This design reduces the total solution cost by avoiding the need to use expensive, high-value capacitors at the LDO output.

6.3.2 Dropout Voltage

The TPS74701-Q1 offers very low dropout performance, making the device designed for high-current, low V_{IN} , low V_{OUT} applications. The low dropout of the TPS74701-Q1 allows the device to be used in place of a DC/DC converter and still achieve good efficiency. This feature provides designers with the power architecture for their applications to achieve the smallest, simplest, and lowest cost solution.

There are two different specifications for dropout voltage with the TPS74701-Q1. The first specification (shown in [Figure 6-1](#)) is referred to as V_{IN} dropout and is used when an external bias voltage is applied to achieve low dropout. This specification assumes that V_{BIAS} is at least 1.62 V above V_{OUT} , which is the case for V_{BIAS} when powered by a 3.3-V rail with 5% tolerance and with $V_{OUT} = 1.5$ V. If V_{BIAS} is higher than $V_{OUT} + 1.62$ V, V_{IN} dropout is less than specified.

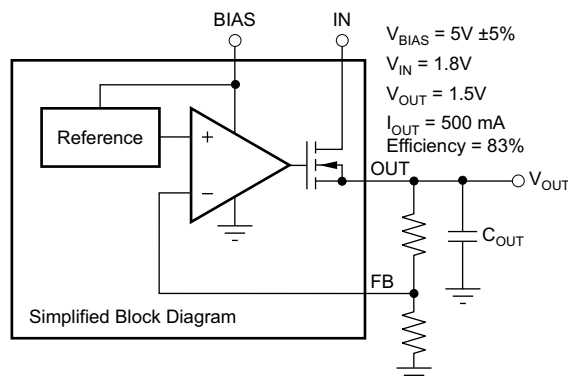


Figure 6-1. Typical Application of the TPS74701-Q1 Using an Auxiliary Bias Rail

The second specification (shown in [Figure 6-2](#)) is referred to as V_{BIAS} dropout and applies to applications where IN and BIAS are tied together. This option allows the device to be used in applications where an auxiliary bias voltage is not available or low dropout is not required. Dropout is limited by BIAS in these applications because V_{BIAS} provides the gate drive to the pass transistor; therefore, V_{BIAS} must be 1.39 V above V_{OUT} for the legacy chip or 1.3 V for the new chip¹. Because of this usage, IN and BIAS tied together easily consume huge power. Pay attention not to exceed the power rating of the device package.

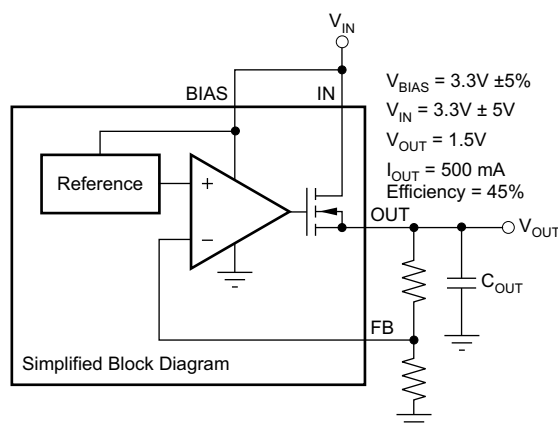


Figure 6-2. Typical Application of the TPS74701-Q1 Without an Auxiliary Bias Rail

¹ See the [Device Nomenclature](#) and [Electrical Characteristics](#) for more information regarding the legacy chip and new chip

6.3.3 Output Noise

The TPS74701-Q1 provides low output noise when a soft-start capacitor is used. When the device reaches the end of the soft-start cycle, the soft-start capacitor serves as a filter for the internal reference. By using a 0.001-μF soft-start capacitor, the output noise is reduced by half and is typically 30 μV_{RMS} for a 1.2-V output (10 Hz to 100 kHz) for the legacy chip and 24 μV_{RMS} for a 1.2-V output (10 Hz to 100 kHz) with the new chip. Further increasing C_{SS} has little effect on noise. Because most of the output noise is generated by the internal reference, the noise is a function of the set output voltage. The RMS noise with a 0.001-μF soft-start capacitor is given in the following equations:

$$V_N = 25 \left(\frac{\mu V_{RMS}}{V} \right) \times V_{OUT} (V) \text{ (Legacy Chip)} \quad (1)$$

$$V_N = 20 \left(\frac{\mu V_{RMS}}{V} \right) \times V_{OUT} (V) \text{ (New Chip)} \quad (2)$$

The low output noise of the TPS74701-Q1 makes the device a good choice for powering transceivers, PLLs, or other noise-sensitive circuitry.

6.3.4 Enable and Shutdown

The enable (EN) pin is active high and is compatible with standard digital signaling levels. V_{EN} below 0.4 V turns the regulator off, while V_{EN} above 1.1 V turns the regulator on. Unlike many regulators, the enable circuitry has hysteresis and deglitching for use with relatively slowly ramping analog signals. This configuration allows the TPS74701-Q1 to be enabled by connecting the output of another supply to the EN pin. The enable circuitry typically has 50 mV of hysteresis and a deglitch circuit to help avoid on and off cycling as a result of small glitches in the V_{EN} signal.

The enable threshold is typically 0.8 V and varies with temperature and process variations. Temperature variation is approximately –1 mV/°C; process variation accounts for most of the rest of the variation to the 0.4-V and 1.1-V limits. If precise turn-on timing is required, a fast rise-time signal must be used to enable the TPS74701-Q1.

If not used, EN can be connected to either IN or BIAS. If EN is connected to IN, connect this pin as close as possible to the largest capacitance on the input to prevent voltage droops on that line from triggering the enable circuit.

6.3.5 Power Good

The power-good (PG) pin is an open-drain output and can be connected to any 5.5 V or lower rail through an external pullup resistor. This pin requires at least 1.1 V on V_{BIAS} to have a valid output. The PG output is high-impedance when V_{OUT} is greater than V_{IT} + V_{HYS}. If V_{OUT} drops below V_{IT} or if V_{BIAS} drops below 1.9 V, the open-drain output turns on and pulls the PG output low. The PG pin also asserts when the device is disabled. The recommended operating condition of the PG pin sink current is up to 1 mA, so the pullup resistor for PG must be in the range of 10 kΩ to 1 MΩ. If output voltage monitoring is not needed, the PG pin can be left floating.

6.3.6 Internal Current Limit

The TPS74701-Q1 features a factory-trimmed, accurate current limit that is flat over temperature and supply voltage. The current limit allows the device to supply surges of up to 1 A and maintain regulation. The current limit responds in approximately 10 μs to reduce the current during a short-circuit fault.

The internal current limit protection circuitry of the TPS74701-Q1 is designed to protect against overload conditions. This circuitry is not intended to allow operation above the rated current of the device. Continuously running the TPS74701-Q1 above the rated current degrades device reliability.

6.3.7 Thermal Protection

Thermal protection disables the output when the junction temperature rises to approximately 160°C, allowing the device to cool. When the junction temperature cools to approximately 140°C, the output circuitry is enabled.

Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit can cycle on and off. This cycling limits the dissipation of the regulator, protecting the regulator from damage as a result of overheating.

Activation of the thermal protection circuit indicates excessive power dissipation or inadequate heat sinking. For reliable operation, limit junction temperature to 125°C maximum. To estimate the margin of safety in a complete design (including heat sink), increase the ambient temperature until thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection must trigger at least 40°C above the maximum expected ambient condition of the application. This condition produces a worst-case junction temperature of 125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS74701-Q1 is designed to protect against overload conditions. This circuitry is not intended to replace proper heat sinking. Continuously running the TPS74701-Q1 into thermal shutdown degrades device reliability.

6.4 Device Functional Modes

6.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage and bias voltage are both at least at the respective minimum specifications
- The enable voltage has previously exceeded the enable rising threshold voltage and has not decreased below the enable falling threshold
- The output current is less than the current limit
- The device junction temperature is less than the maximum specified junction temperature

6.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this condition, the output voltage is the same as the input voltage minus the dropout voltage. The transient performance of the device is significantly degraded because the pass transistor is in a triode state and no longer controls the current through the LDO. Line or load transients in dropout can result in large output voltage deviations.

6.4.3 Disabled

The device is disabled under the following conditions:

- The input or bias voltages are below the respective minimum specifications.
- The enable voltage is less than the enable falling threshold voltage or has not yet exceeded the enable rising threshold.
- The device junction temperature is greater than the thermal shutdown temperature.

表 6-1 shows the conditions that lead to the different modes of operation.

表 6-1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER				
	V_{IN}	V_{EN}	V_{BIAS}	I_{OUT}	T_J
Normal mode	$V_{IN} > V_{OUT(nom)} + V_{DO}$ (V_{IN})	$V_{EN} > V_{EN, HI}$	$V_{BIAS} \geq V_{OUT} + 1.39\text{ V}$	$I_{OUT} < I_{CL}$	$T_J < 125^\circ\text{C}$
Dropout mode	$V_{IN} < V_{OUT(nom)} + V_{DO}$ (V_{IN})	$V_{EN} > V_{EN, HI}$	$V_{BIAS} < V_{OUT} + 1.39\text{ V}$	—	$T_J < 125^\circ\text{C}$
Disabled mode (any true condition the device)	$V_{IN} < V_{IN(min)}$	$V_{EN} < V_{EN, LO}$	$V_{BIAS} < V_{BIAS(min)}$	—	$T_J > 165^\circ\text{C}$

7 Application and Implementation

注

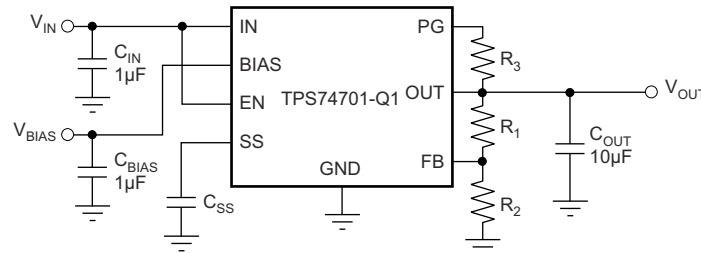
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7.1 Application Information

The TPS74701-Q1 is a 500-mA low-dropout regulator with soft-start function integrated. Based on the end-application, different output voltage could be achieved with different values of external components.

7.2 Typical Application

図 7-1 shows the typical application circuit for the TPS74701-Q1 adjustable output device.



$$V_{OUT} = 0.8 \times \left(1 + \frac{R_1}{R_2}\right)$$

図 7-1. Typical Application Circuit for the TPS74701-Q1

R_1 and R_2 can be calculated for any output voltage using the formula shown in 図 7-1. See 表 7-2 for sample resistor values of common output voltages. To achieve the maximum accuracy specifications, R_2 must be less than or equal to 4.99 kΩ.

7.2.1 Design Requirements

For this design example, use the parameters in 表 7-1.

表 7-1. Design Parameters

PARAMETER	EXAMPLE VALUE
Input voltage	1.8 V ± 10%
Output voltage	1.5 V ± 3%
Enable voltage	1.8 V ± 10%
BIAS voltage	3.3 V ± 10%
Output current	500 mA
Output capacitor	10 µF
Start-up time	<2 ms

7.2.2 Detailed Design Procedure

- Select R_1 and R_2 based on the required output voltage. 表 7-2 gives example calculations for many common output voltages.
- Select C_{SS} to be the highest capacitance while still achieving the desired start-up time. 表 7-3 gives examples of this calculation. 図 7-3 gives examples of turn-on response with different C_{SS} capacitor value.

3. Select a minimum of a 2.2-μF ceramic output capacitor. Increased output capacitance helps the output load transient response. [Figure 7-4](#) gives examples of the load transient response with different output capacitor values and types.

7.2.2.1 Input, Output, and Bias Capacitor Requirements

The device is designed to be stable for all available types and values of output capacitors greater than or equal to 2.2 μF. The device is also stable with multiple capacitors in parallel, which can be of any type or value.

The capacitance required on the IN and BIAS pins strongly depends on the input supply source impedance. To counteract any inductance in the input, the minimum recommended capacitor for V_{IN} and V_{BIAS} is 1 μF. If V_{IN} and V_{BIAS} are connected to the same supply, the recommended minimum capacitor for V_{BIAS} is 4.7 μF. Good-quality, low-ESR capacitors must be used on the input; ceramic X5R and X7R capacitors are preferred. These capacitors must be placed as close to the pins as possible for optimum performance.

表 7-2. Standard 1% Resistor Values for Programming the Output Voltage⁽¹⁾

R_1 (kΩ)	R_2 (kΩ)	V_{OUT} (V)
Short	Open	0.8
0.619	4.99	0.9
1.13	4.53	1
1.37	4.42	1.05
1.87	4.99	1.1
2.49	4.99	1.2
4.12	4.75	1.5
3.57	2.87	1.8
3.57	1.69	2.5
3.57	1.15	3.3

$$(1) \quad V_{OUT} = 0.8 \times \left(1 + \frac{R_1}{R_2} \right)$$

表 7-3. Standard Capacitor Values for Programming the Soft-Start Time⁽¹⁾

C_{SS}	SOFT-START TIME (Legacy Chip)	SOFT-START TIME (New Chip)
Open	0.1 ms	0.25 ms
270 pF	0.5 ms	0.4 ms
560 pF	1 ms	0.8 ms
2.7 nF	5 ms	4.1 ms
5.6 nF	10 ms	8.5 ms
0.01 μF	18 ms	15 ms

$$(1) \quad t_{SS}(s) = \frac{0.8 \times C_{SS}(F)}{I_{SS}(A)}$$

7.2.2.2 Programmable Soft-Start

The TPS74701-Q1 features a programmable, monotonic, voltage-controlled soft-start that is set with an external capacitor (C_{SS}). This feature is important for many applications because this capacitor eliminates power-up initialization problems when powering FPGAs, DSPs, or other processors. The controlled voltage ramp of the output also reduces peak inrush current during start-up, minimizing start-up transient events to the input power bus.

To achieve a linear and monotonic soft start, the TPS74701-Q1 error amplifier tracks the voltage ramp of the external soft-start capacitor until the voltage exceeds the internal reference. The soft-start ramp time depends on the soft-start charging current (I_{SS}), soft-start capacitance (C_{SS}), and the internal reference voltage (V_{REF}), and can be calculated using [Equation 3](#):

$$t_{SS} = \frac{(V_{REF} \times C_{SS})}{I_{SS}} \quad (3)$$

If large output capacitors are used, the device current limit (I_{CL}) and the output capacitor can set the start-up time. In this case, the start-up time is given by 式 4:

$$t_{SSCL} = \frac{(V_{OUT(NOM)} \times C_{OUT})}{I_{CL(MIN)}} \quad (4)$$

where:

- $V_{OUT(NOM)}$ is the nominal output voltage
- C_{OUT} is the output capacitance
- $I_{CL(MIN)}$ is the minimum current limit for the device

In applications where monotonic start-up is required, the soft-start time given by 式 3 must be set greater than 式 4.

The maximum recommended soft-start capacitor is 0.015 μ F. Larger soft-start capacitors can be used and do not damage the device; however, the soft-start capacitor discharge circuit can possibly be unable to fully discharge the soft-start capacitor when enabled. Soft-start capacitors larger than 0.015 μ F can be a problem in applications where the enable pin must be rapidly pulsed and still require the device to soft-start from ground. C_{SS} must be low-leakage; X7R, X5R, or C0G dielectric materials are preferred. See 表 7-3 for suggested soft-start capacitor values.

7.2.2.3 Sequencing Requirements

V_{IN} , V_{BIAS} , and V_{EN} can be sequenced in any order without causing damage to the device. However, for the soft-start function to work as intended, certain sequencing rules must be applied. Connecting EN to IN is acceptable for most applications, as long as V_{IN} is greater than 1.1 V and the ramp rate of V_{IN} and V_{BIAS} is faster than the set soft-start ramp rate. If the ramp rate of the input sources is slower than the set soft-start time, the output tracks the slower supply minus the dropout voltage until reaching the set output voltage. If EN is connected to BIAS, the device soft-starts as programmed, provided that V_{IN} is present before V_{BIAS} . If V_{BIAS} and V_{EN} are present before V_{IN} is applied and the set soft-start time has expired, then V_{OUT} tracks V_{IN} . If the soft-start time has not expired, the output tracks V_{IN} until V_{OUT} reaches the value set by the charging soft-start capacitor. 図 7-2 shows the use of an RC delay circuit to hold off V_{EN} until V_{BIAS} has ramped. This technique can also be used to drive EN from V_{IN} . An external control signal can also be used to enable the device after V_{IN} and V_{BIAS} are present.

注

When V_{BIAS} and V_{EN} are present and V_{IN} is not supplied, this device outputs approximately 50 μ A of current from OUT. Although this condition does not cause any damage to the device, the output current can charge up the OUT node if total resistance between OUT and GND (including external feedback resistors) is greater than 10 k Ω .

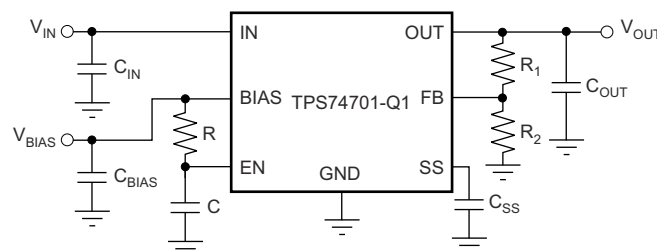
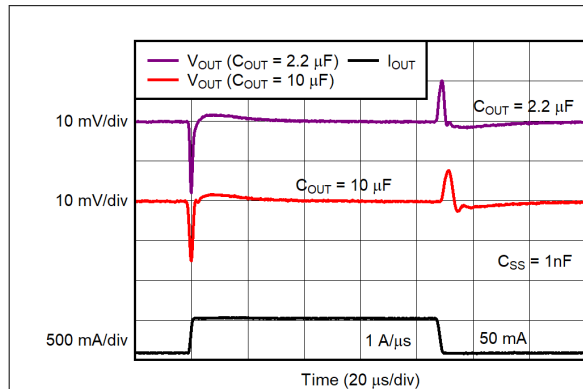
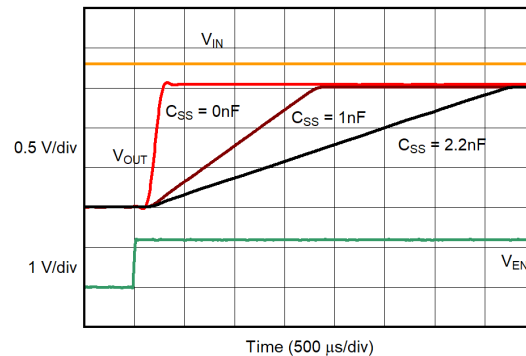


図 7-2. Soft-Start Delay Using an RC Circuit to Enable the Device

7.2.3 Application Curves



✎ 7-3. Output Load Transient Response



✎ 7-4. Turn-On Response

7.3 Power Supply Recommendations

The TPS74701-Q1 is designed to operate from an input voltage up to 5.5 V, provided the bias rail is at least 1.39 V higher than the input supply and dropout requirements are met. The bias rail and the input supply must both provide adequate headroom and current for the device to operate normally.

Connect a low-output impedance power supply directly to the IN pin of the TPS74701. This supply must have at least 1 μF of capacitance near the IN pin for optimal performance. A supply with similar requirements must also be connected directly to the bias rail with a separate 1 μF or larger capacitor. If the IN pin is tied to the bias pin, a minimum 4.7 μF of capacitance is needed for performance. To increase the overall PSRR of the solution at higher frequencies, use a pi-filter or ferrite bead before the input capacitor.

7.4 Layout

7.4.1 Layout Guidelines

7.4.1.1 Layout Recommendations and Power Dissipation

An optimal layout can greatly improve transient performance, PSRR, and noise. To minimize the voltage drop on the input of the device during load transients, the capacitance on IN and BIAS must be connected as close as possible to the device. This capacitance also minimizes the effects of parasitic inductance and resistance of the input source and can, therefore, improve stability. To achieve optimal transient performance and accuracy, the top side of R_1 in [✎ 7-1](#) must be connected as close as possible to the load. If BIAS is connected to IN, connect BIAS as close to the sense point of the input supply as possible. This connection minimizes the voltage drop on BIAS during transient conditions and can improve the turn-on response.

Knowing the device power dissipation and proper sizing of the thermal plane that is connected to the thermal pad is critical to avoiding thermal shutdown and to provide reliable operation. Power dissipation of the device depends on input voltage and load conditions and can be calculated using [式 5](#):

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (5)$$

Power dissipation can be minimized and greater efficiency can be achieved by using the lowest possible input voltage necessary to achieve the required output voltage regulation.

The primary conduction path for heat is through the exposed pad to the printed circuit board (PCB). The pad can be connected to ground or be left floating; however, the pad must be attached to an appropriate amount of copper PCB area to make sure the device does not overheat. The maximum junction-to-ambient thermal resistance depends on the maximum ambient temperature, maximum device junction temperature, and power dissipation of the device and can be calculated using [式 6](#):

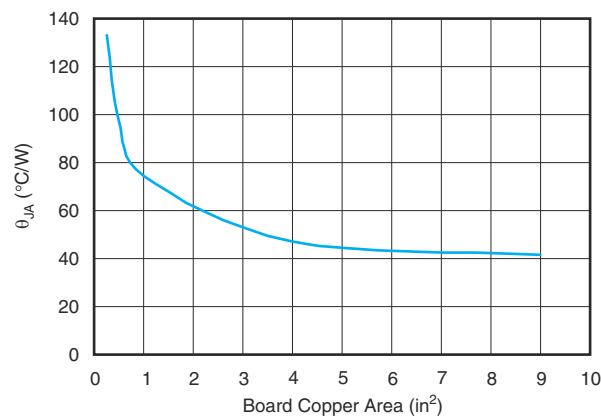
$$R_{\theta JA} = \frac{(150^{\circ}\text{C} - T_A)}{P_D} \quad (6)$$

Knowing the maximum $R_{\theta JA}$, the minimum amount of PCB copper area needed for appropriate heat sinking can be estimated using 図 7-5.

図 7-5 shows the variation of $R_{\theta JA}$ as a function of ground plane copper area in the board. This figure is intended only as a guideline to demonstrate the effects of heat spreading in the ground plane and is not intended to be used to estimate actual thermal performance in real application environments.

注

When the device is mounted on an application PCB, use Ψ_{JT} and Ψ_{JB} , as explained in the [Estimating Junction Temperature](#) section.



$R_{\theta JA}$ value at board size of 9 in² (that is, 3-in × 3-in) is a JEDEC standard.

図 7-5. $R_{\theta JA}$ vs Board Size

7.4.1.2 Estimating Junction Temperature

Using the thermal metrics Ψ_{JT} and Ψ_{JB} , as shown in the [Thermal Information](#) table, the junction temperature can be estimated with corresponding formulas (given in 式 7). For backwards compatibility, an older $R_{\theta JC, Top}$ parameter is listed as well.

$$\begin{aligned} \Psi_{JT}: T_J &= T_T + \Psi_{JT} \cdot P_D \\ \Psi_{JB}: T_J &= T_B + \Psi_{JB} \cdot P_D \end{aligned} \quad (7)$$

Where P_D is the power dissipation shown by 式 7, T_T is the temperature at the center-top of the device package, and T_B is the PCB temperature measured 1 mm away from the device package *on the PCB surface* (see 図 7-7).

注

Both T_T and T_B can be measured on actual application boards using a thermo-gun (an infrared thermometer).

For more information about measuring T_T and T_B , see the [Using New Thermal Metrics application note](#), available for download at www.ti.com.

In reference to 図 7-6, the new thermal metrics (Ψ_{JT} and Ψ_{JB}) have very little dependency on board size. That is, using Ψ_{JT} or Ψ_{JB} with 式 7 is a good way to estimate T_J by simply measuring T_T or T_B , regardless of the application board size.

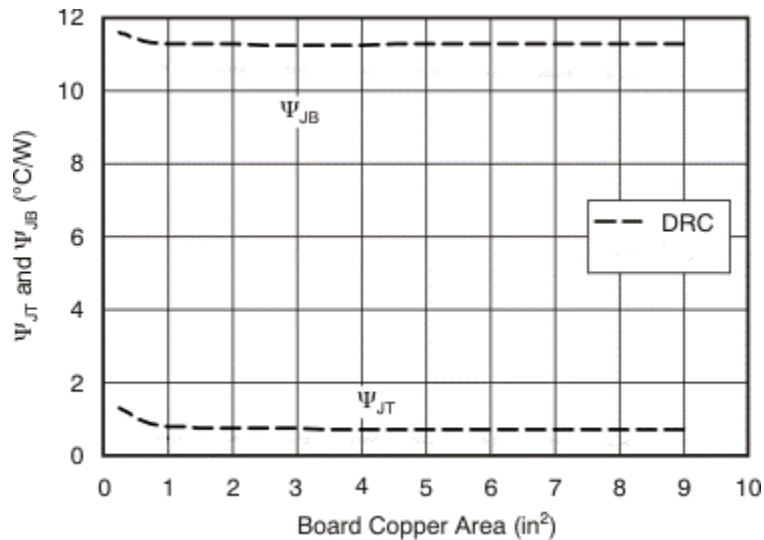
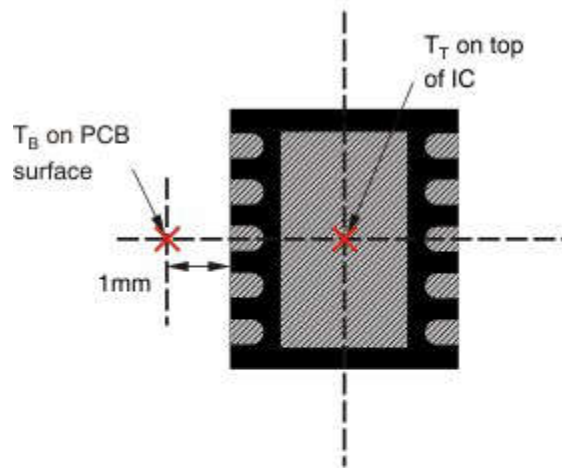


図 7-6. Ψ_{JT} and Ψ_{JB} vs Board Size

For a more detailed discussion of why TI does not recommend using $R_{\theta JC(top)}$ to determine thermal characteristics, see the [Using New Thermal Metrics application note](#), available for download at www.ti.com. For further information, see the [Semiconductor and IC Package Thermal Metrics application note](#), also available on the TI website.

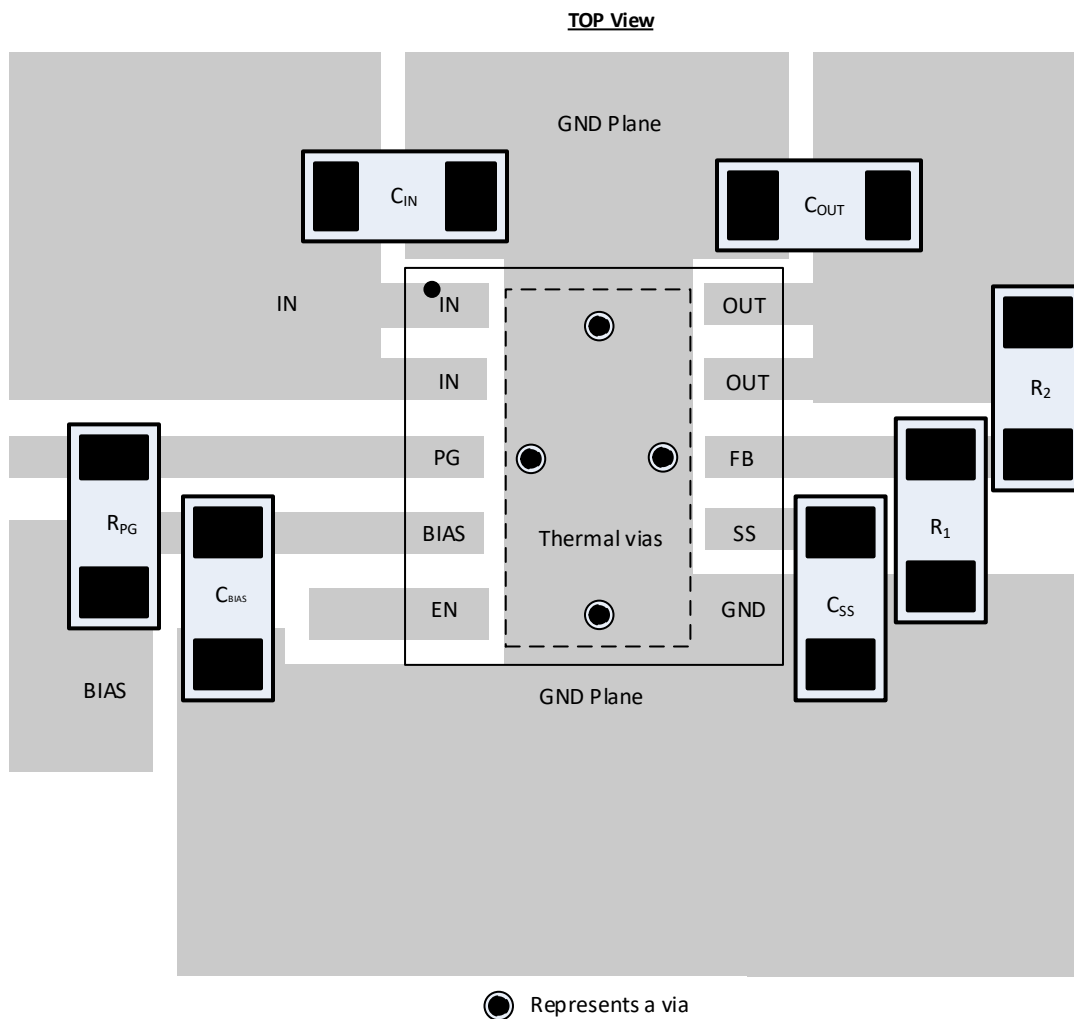


(a) Example DRC (SON) Package Measurement

- A. T_T is measured at the center of both the X- and Y-dimensional axes.
- B. T_B is measured *below* the package lead on the PCB surface.

図 7-7. Measuring Points for T_T and T_B

7.4.2 Layout Example



7-8. Layout Example: DRC Package

8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

For development support, see the following:

- Texas Instruments, [TPS74801-Q1 1.5 A Low-Dropout Linear Regulator with Programmable Soft-Start data sheet](#)
- Texas Instruments, [TI PCB Thermal Calculator](#)

8.1.2 Device Nomenclature

表 8-1. Device Nomenclature

PRODUCT ⁽¹⁾	DESCRIPTION
TPS74701QyyyzM3Q1	Q indicates that this device is a grade-1 device in accordance with the AEC-Q100 standard. yyy is the package designator. z is the package quantity. M3 is a suffix designator for devices that only use the latest manufacturing flow (CSO: RFB). Devices without this suffix can ship with the legacy chip (CSO: DLN) or the new chip (CSO: RFB). The reel packaging label provides CSO information to distinguish which chip is used. Device performance for new and legacy chips is denoted throughout the document. Q1 indicates that this device is an automotive grade (AEC-Q100) device.

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or visit the device product folder on www.ti.com.

8.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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8.6 用語集

[テキサス・インスツルメンツ用語集](#)

この用語集には、用語や略語の一覧および定義が記載されています。

9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (October 2023) to Revision D (December 2023)	Page
• 従来のチップと新しいチップの情報を区別するため、ドキュメント全体にデバイスの言い回しを追加.....	1
• ターンオン応答プロットを更新し、新しいチップの性能を表示.....	1
• Changed <i>Typical Characteristics</i> sections to show legacy chip and new chip data side by side and deleted V_{IN} Dropout Voltage vs $V_{BIAS}-V_{OUT}$ curves.....	8
• Added soft-start time for new chip in <i>Standard Capacitor Values for Programming the Soft-Start Time</i> table.....	20
• Changed <i>Device Nomenclature</i> section.....	26

Changes from Revision B (September 2016) to Revision C (October 2023)	Page
• ドキュメント全体にわたって表、図、相互参照の採番方法を更新	1
• ドキュメントに M3 固有デバイスを追加.....	1
• 「特長」の車載特有の箇条書き項目を変更	1
• 「特長」の「 V_{IN} 範囲」、「低ドロップアウト」、「精度」、「パッケージ」の箇条書き項目を変更: 「 V_{IN} 範囲」の箇条書き項目から「超低」を削除、「低ドロップアウト」の箇条書き項目で 50mV を 20mV に変更、「精度」の箇条書き項目で 2% を 0.95% に変更、パッケージの箇条書き項目から × 1mm を削除	1
• 「アプリケーション」セクションを変更	1
• 「概要」セクションを変更	1
• Changed <i>Description</i> column of <i>Pin Functions</i> table.....	3
• Changed <i>Typical Characteristics</i> and added new <i>Typical Characteristics</i> sections.....	8
• Changed footnote for <i>Standard Capacitor Values for Programming the Soft-Start Time</i> table.....	20
• Changed <i>Layout</i> section.....	22
• Added <i>Device Nomenclature</i> section.....	26

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS74701QDRCRM3Q1	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	PAE
TPS74701QDRCRM3Q1.A	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	PAE
TPS74701QDRCRQ1	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	PAE
TPS74701QDRCRQ1.A	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 150	PAE

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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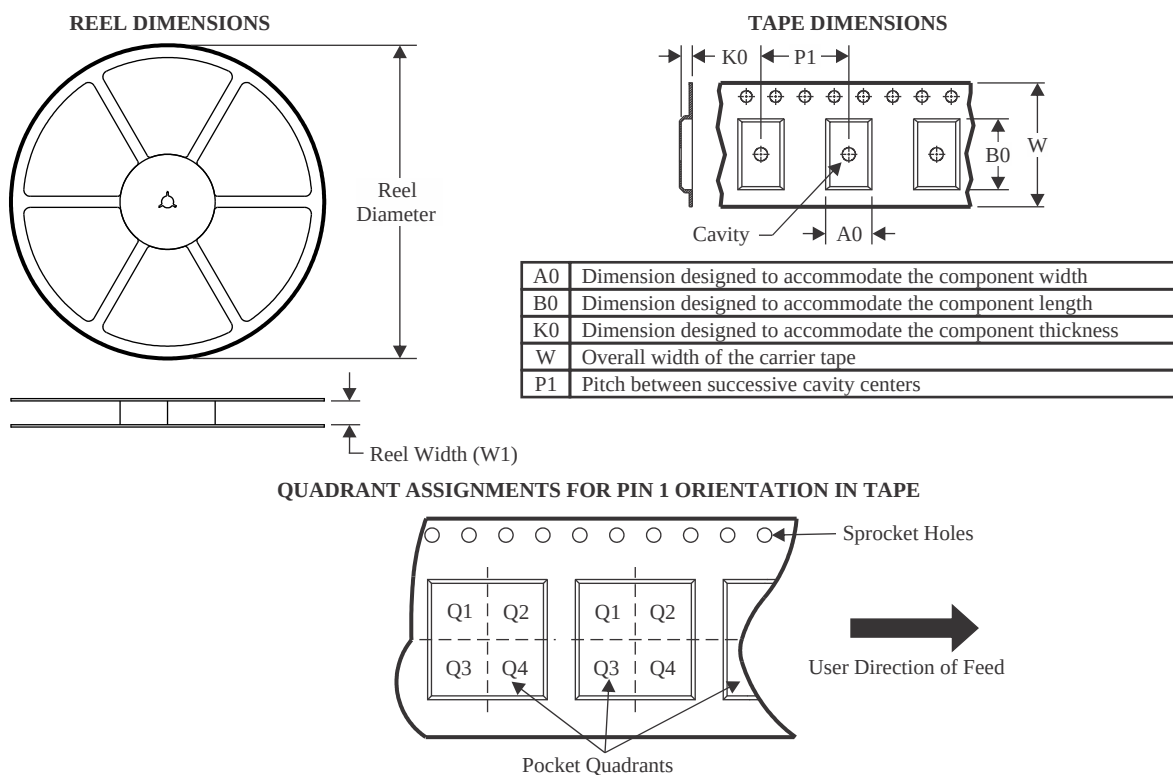
OTHER QUALIFIED VERSIONS OF TPS74701-Q1 :

- Catalog : [TPS74701](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

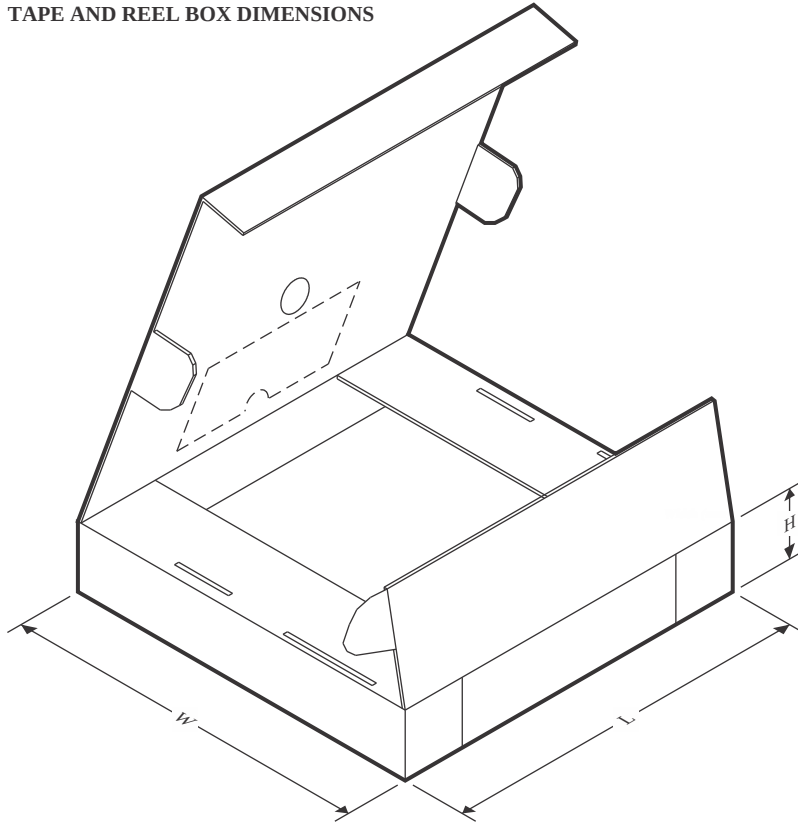
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS74701QDRCRM3Q1	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS74701QDRCRQ1	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS74701QDRCRM3Q1	VSON	DRC	10	3000	367.0	367.0	35.0
TPS74701QDRCRQ1	VSON	DRC	10	3000	367.0	367.0	35.0

GENERIC PACKAGE VIEW

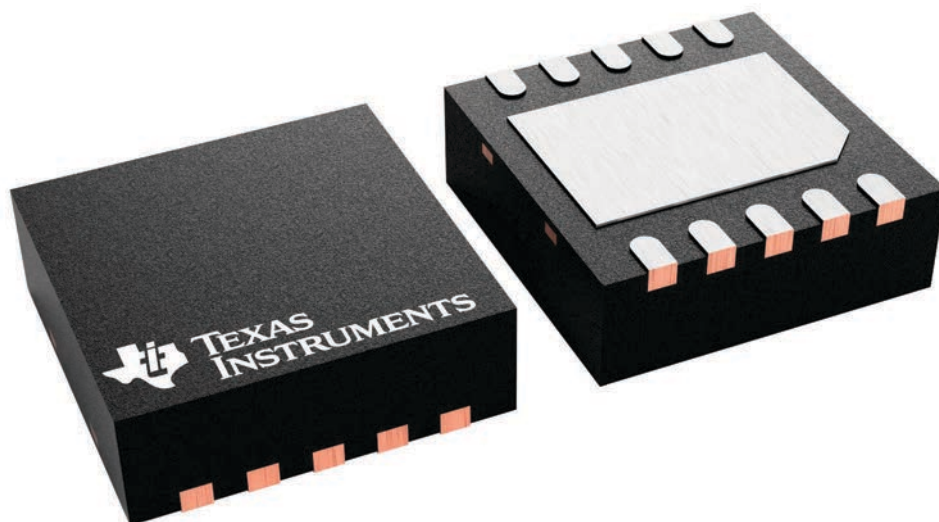
DRC 10

VSON - 1 mm max height

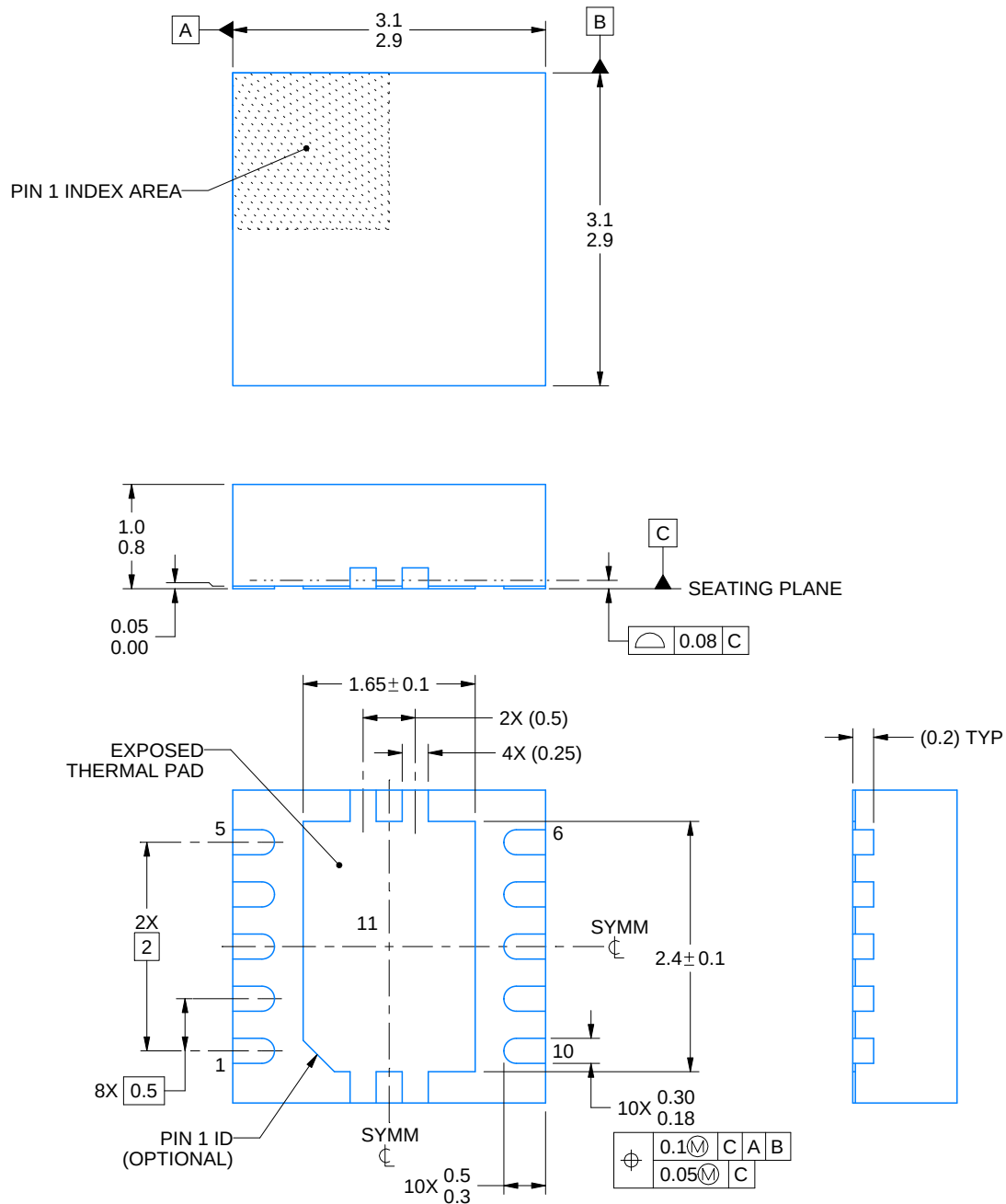
3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4226193/A



4218878/B 07/2018

NOTES:

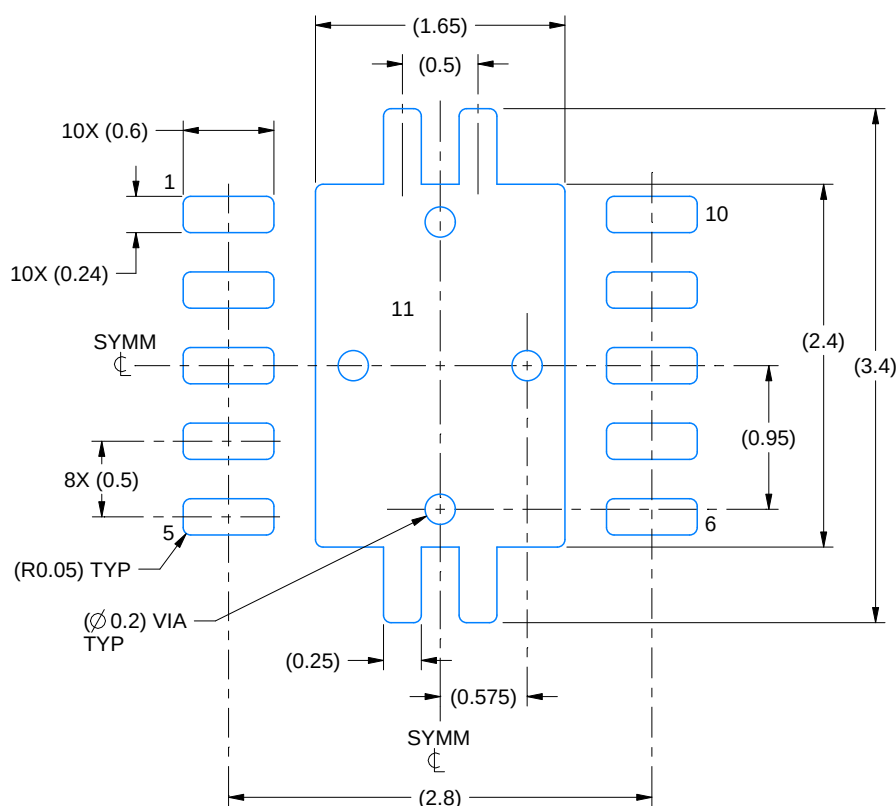
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

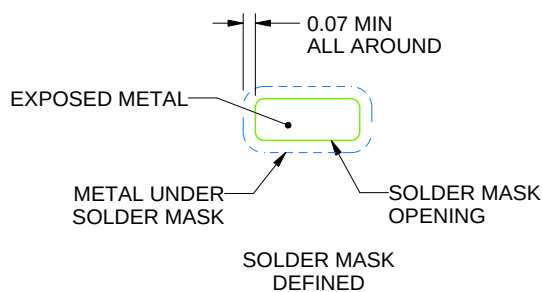
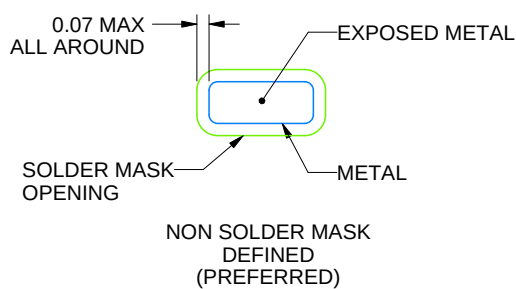
DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4218878/B 07/2018

NOTES: (continued)

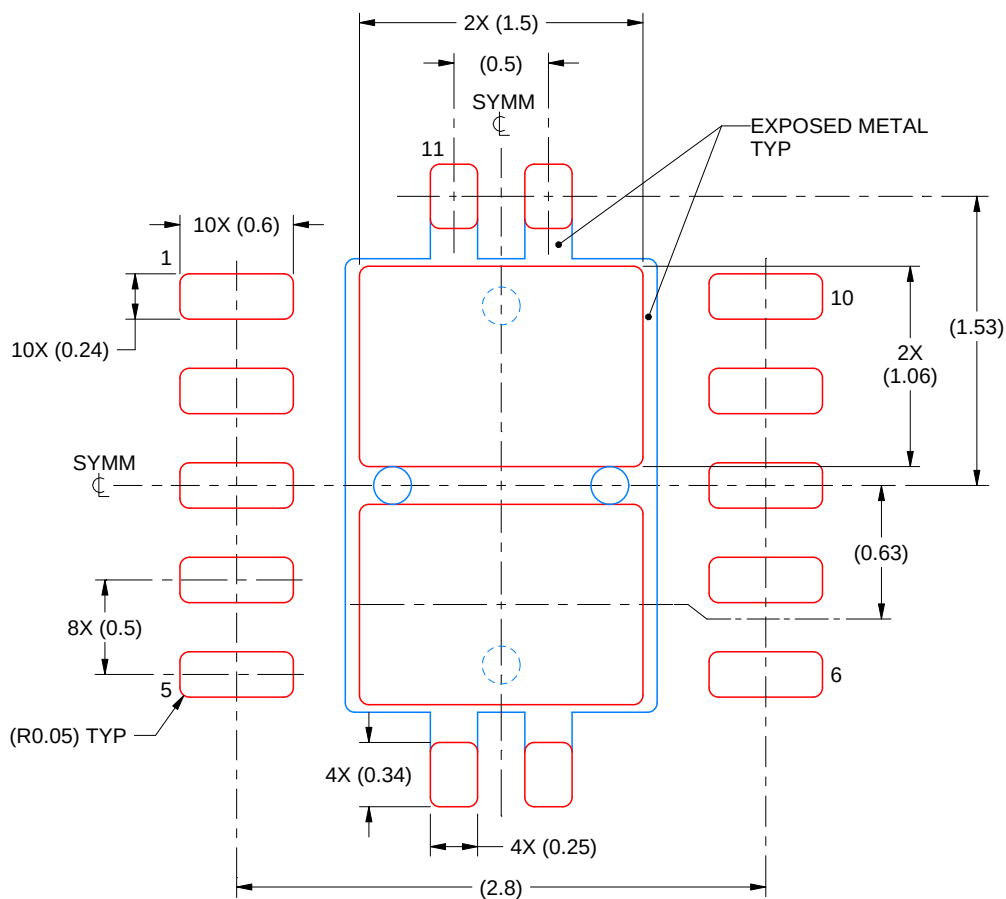
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218878/B 07/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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